MICRO ELECTRONICS

2N3417

NPN
SILICON
TRANSISTOR

TO-92

ECB

2N3417 is NPN silicon planar transistor designed for general purpose AF medium power applications.

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	50V
Collector-Emitter Voltage	VCEO	50V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	500mA
Total Power Dissipation	Tj,Tstg	-55 to +150°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BVCBO	50		V	IC=100μA IE=0
Collector-Emitter Breakdown Voltage	BVCEO	50		V	IC=10mA IB=0
Emitter-Base Breakdown Voltage	BVEBO	5		V	IE=10μA IC=0
Collector Cutoff Current	ICBO		100	nA	VCB=50V IE=0
Emitter Cutoff Current	IEBO		100	nA	VEB=5V IC=0
D.C. Current Gain	HFE	180	540		IC=2mA VCE=4.5V
Collector-Emitter Saturation Voltage	VCE(sat)		0.3	V	IC=50mA IB=3mA
Base-Emitter Saturation Voltage	VBE(sat)		0.85	V	IC=50mA IB=3mA
Small Signal Current Gain	hfe	300	TYP		IC=1mA VCE=10V f=1KHz

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